

Congratulations to the 16 Newly Elected IEEE Electron Devices Society Fellows

Effective January 1, 2021

Deji Akinwande

for contributions to wafer-scale graphene synthesis and application to flexible devices

Hideaki Aochi

for contributions to three dimensional flash memories

Benton Calhoun

for contributions to sub-threshold integrated circuits and self-powered systems

Yogesh Chauhan

for contributions to compact modeling of Si and GaN transistors

Vasilis Fthenakis

for contributions to photovoltaics technology

Robert Henderson

for contributions to solid-state single photon imaging

Ali Keshavarzi

for contributions to low-power circuits and devices in scaled CMOS technologies

Chang-jin Kim

for research of surface-tension-based microelectromechanical

Gourab Majumdar

for contribution to power semiconductor devices and intelligent power module

Jun Ohta

for contributions to CMOS image sensors and devices for biomedical applications

Bryan Root

for leadership in improving semiconductor reliability test methods

Ashwin Seshia

for contributions to resonant-based inertial and mode-localized sensors

Tetsuya Suemitsu

for contributions to high-frequency high-electron-mobility transistors

Takatoshi Tsujimura

for contributions to the development of organic-light-emitting diode systems

Yifeng Wu

for contributions to Gallium Nitride microwave and power conversion devices

Shinji Yuasa

for contributions to MgO-based magnetic tunnel junctions

*Samar Saha
EDS Fellows Chair*